

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 Volts (Typ) @ $I_F = 10 \text{ mA}$



BAT54HT1

**30 VOLT SILICON
HOT-CARRIER DETECTOR
AND SWITCHING DIODES**



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
BAT54HT1	SOD-323	3000/Tape & Reel

Preferred: devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	V

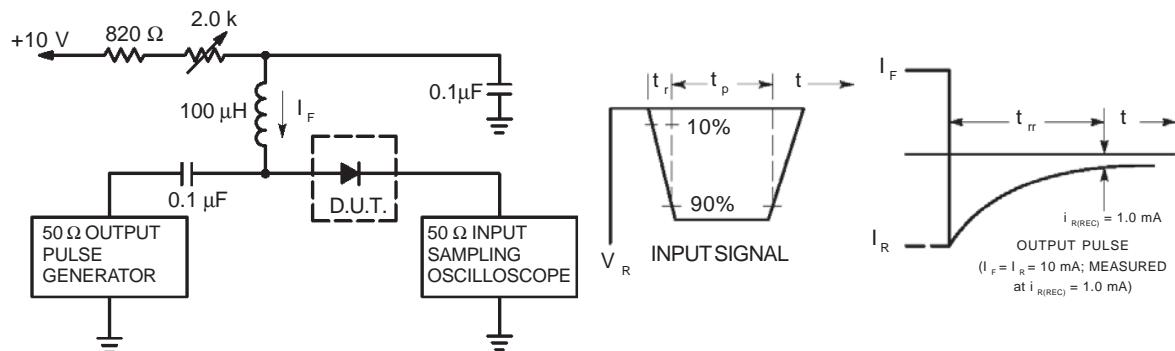
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,*	P _D	200	mW
T _A = 25°C			
Derate above 25°C		1.57	mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	635	°C/W
Junction and Storage Temperature Range	T _J , T _{sg}	150	°C

*FR-5 Minimum Pad

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	30	—	—	Volts
Total Capacitance (V _R = 1.0 V, f = 1.0 MHz)	C _T	—	7.6	10	pF
Reverse Leakage (V _R = 25 V)	k	—	0.5	2.0	μA
Forward Voltage (I _F = 0.1 mA)	V _F	—	0.22	0.24	Vdc
Forward Voltage (I _F = 30 mA)	V _F	—	0.41	0.5	Vdc
Forward Voltage (I _F = 100 mA)	V _F	—	0.52	1.0	Vdc
Reverse Recovery Time (I _F = I _R = 10 mA, I _(REC) = 1.0 mA, Figure 1)	t _{rr}	—	—	5.0	ns
Forward Voltage (I _F = 1.0 mA)	V _F	—	0.29	0.32	Vdc
Forward Voltage (I _F = 10 mA)	V _F	—	0.35	0.40	Vdc
Forward Current (DC)	I _F	—	—	200	mA
Repetitive Peak Forward Current	I _{FRM}	—	—	300	mA
Non-Repetitive Peak Forward Current (t < 1.0 s)	I _{FSM}	—	—	600	mA

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Figure 1. Recovery Time Equivalent Test Circuit
